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(54) Title: METHOD AND DEVICE FOR MANUFACTURING HYDROPHILIC SUBSTRATE

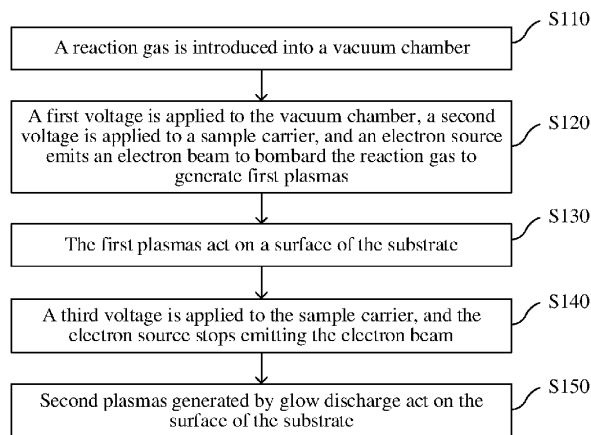


FIG. 1

(57) Abstract: A method and a device for manufacturing a hydrophilic substrate are provided. The method includes introducing reaction gas into vacuum chamber; applying first voltage to the vacuum chamber, applying second voltage to sample carrier, and emitting, by an electron source, electron beam to bombard the reaction gas to generate the first plasmas; enabling the first plasmas to act on surface of the substrate; applying third voltage to the sample carrier; enabling the electron source to stop emitting the electron beam; and enabling second plasmas generated by glow discharge to act on the surface of the substrate. By the method for manufacturing the hydrophilic substrate provided by the disclosure, it is easy to glow in the processes of generating first plasmas and second plasmas. After the first plasmas and the second plasmas act on the substrate, the hydrophilic effect of the substrate is stable and the defective rate is low.

[Continued on next page]

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